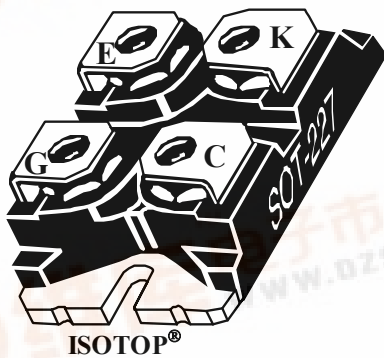
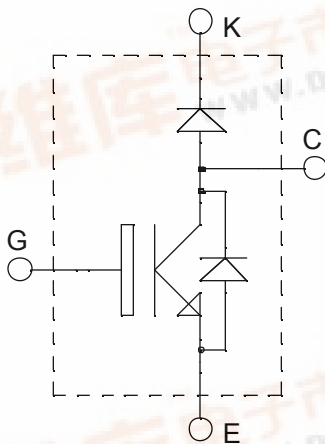


**ISOTOP[®] Boost chopper
NPT IGBT**

**$V_{CES} = 600V$
 $I_C = 50A @ T_c = 90^{\circ}C$**



Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction
- Brake switch

Features

- Non Punch Through (NPT) THUNDERBOLT IGBT[®]
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 100 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - Avalanche energy rated
 - RBSOA and SCSOA rated
- ISOTOP[®] Package (SOT-227)
- Very low stray inductance
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_C of V_{CESat}
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage	600	V
I_{C1}	Continuous Collector Current	$T_C = 25^{\circ}C$	75
I_{C2}		$T_C = 90^{\circ}C$	50
I_{CM}		$T_C = 25^{\circ}C$	160
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Maximum Power Dissipation	$T_C = 25^{\circ}C$	277
I_{LM}	RBSOA clamped Inductive load Current $R_G = 11\Omega$	$T_C = 25^{\circ}C$	100
$I_{F_{AV}}$	Maximum Average Forward Current	$T_C = 80^{\circ}C$	A
$I_{F_{RMS}}$	RMS Forward Current (Square wave, 50% duty)		

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0\text{V}$ $V_{CE} = 600\text{V}$	$T_j = 25^\circ\text{C}$		40	μA
			$T_j = 125^\circ\text{C}$		1000	
$V_{CE(sat)}$	Collector Emitter saturation Voltage	$V_{GE} = 15\text{V}$ $I_C = 50\text{A}$	$T_j = 25^\circ\text{C}$	2.1	2.7	V
			$T_j = 125^\circ\text{C}$	2.2	2.8	
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 700\mu\text{A}$	4.5	5.5	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = \pm 20\text{V}, V_{CE} = 0\text{V}$			± 100	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0\text{V}$ $V_{CE} = 25\text{V}$ $f = 1\text{MHz}$		2250		pF
C_{oes}	Output Capacitance			255		
C_{res}	Reverse Transfer Capacitance			155		
Q_g	Total gate Charge	$V_{GS} = 15\text{V}$ $V_{Bus} = 300\text{V}$ $I_C = 50\text{A}$		175		nC
Q_{ge}	Gate – Emitter Charge			18		
Q_{gc}	Gate – Collector Charge			100		
$T_{d(on)}$	Turn-on Delay Time	Resistive Switching (25°C) $V_{GE} = 15\text{V}$ $V_{Bus} = 300\text{V}$ $I_C = 50\text{A}$ $R_G = 10\Omega$		29		ns
T_r	Rise Time			118		
$T_{d(off)}$	Turn-off Delay Time			150		
T_f	Fall Time			190		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = 15\text{V}$ $V_{Bus} = 400\text{V}$ $I_C = 50\text{A}$ $R_G = 10\Omega$		30		ns
T_r	Rise Time			80		
$T_{d(off)}$	Turn-off Delay Time			240		
T_f	Fall Time			43		
E_{ts}	Total switching Losses			3.6		mJ
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = 15\text{V}$ $V_{Bus} = 400\text{V}$ $I_C = 50\text{A}$ $R_G = 10\Omega$		28		ns
T_r	Rise Time			75		
$T_{d(off)}$	Turn-off Delay Time			265		
T_f	Fall Time			185		mJ
E_{on}	Turn-on Switching Energy			1.8		
E_{off}	Turn-off Switching Energy			2.4		
E_{ts}	Total switching Losses			4.2		

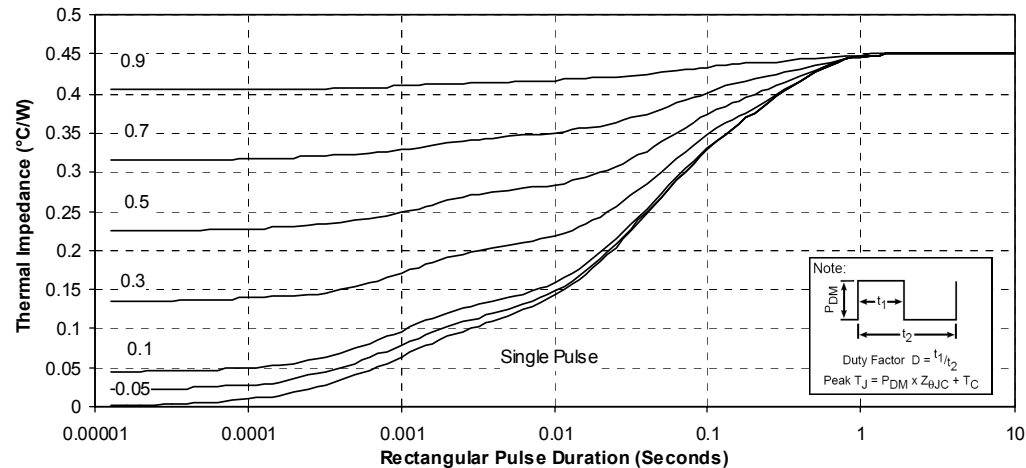
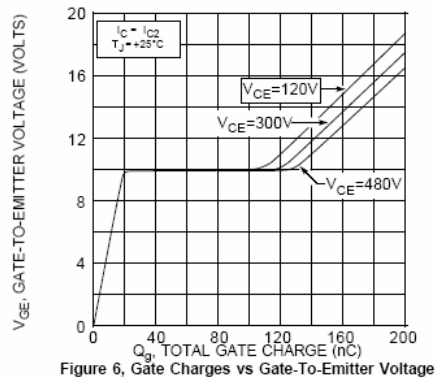
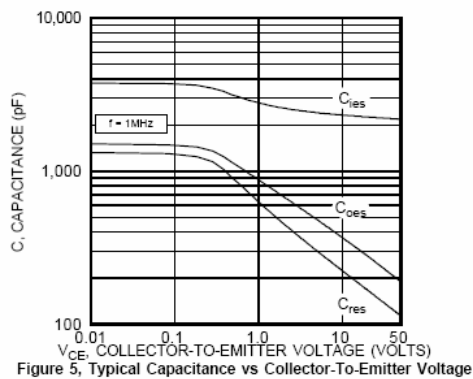
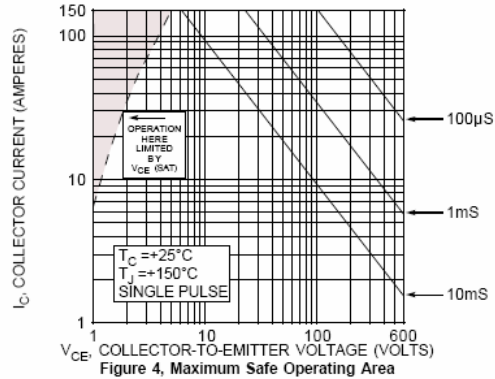
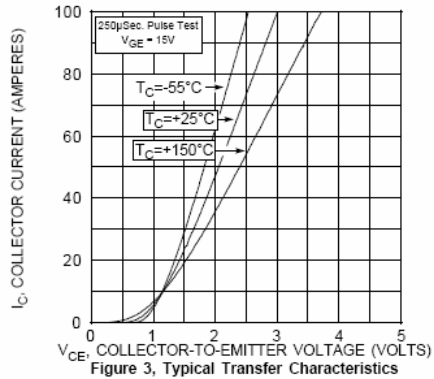
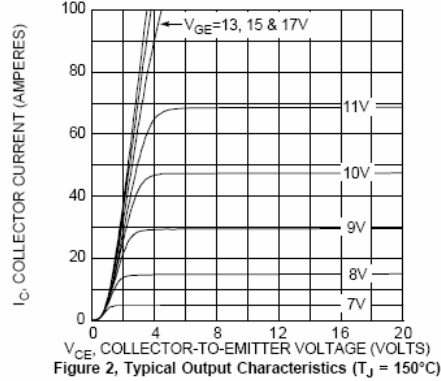
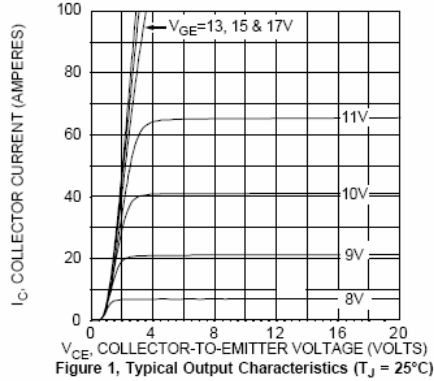
Chopper diode ratings and characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
V _F	Diode Forward Voltage	I _F = 30A		1.6	1.8	V
		I _F = 60A		1.9		
		I _F = 30A	T _j = 125°C		1.4	
I _{RM}	Maximum Reverse Leakage Current	V _R = 600V			250	μA
		V _R = 600V	T _j = 125°C		500	
C _T	Junction Capacitance	V _R = 200V		44		pF
t _{rr}	Reverse Recovery Time	I _F =1A, V _R =30V di/dt =100A/μs	T _j = 25°C		23	ns
	Reverse Recovery Time		T _j = 25°C		85	
I _{RRM}	Maximum Reverse Recovery Current	I _F = 30A V _R = 400V di/dt =200A/μs	T _j = 125°C		160	A
			T _j = 25°C		4	
Q _{rr}	Reverse Recovery Charge		T _j = 125°C		8	nC
			T _j = 25°C		130	
t _{rr}	Reverse Recovery Time	I _F = 30A	T _j = 125°C		70	ns
Q _{rr}	Reverse Recovery Charge	V _R = 400V			1300	nC
I _{RRM}	Maximum Reverse Recovery Current	di/dt =1000A/μs			30	A

Thermal and package characteristics

<i>Symbol</i>	<i>Characteristic</i>		<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
R _{thJC}	Junction to Case Thermal Resistance	IGBT			0.45	°C/W
		Diode			1.21	
R _{thJA}	Junction to Ambient (IGBT & Diode)				20	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I _{isol} <1mA, 50/60Hz		2500			V
T _J , T _{STG}	Storage Temperature Range		-55		150	°C
T _L	Max Lead Temp for Soldering:0.063" from case for 10 sec				300	
Torque	Mounting torque (Mounting = 8-32 or 4mm Machine and terminals = 4mm Machine)				1.5	N.m
Wt	Package Weight			29.2		g

Typical IGBT Performance Curve



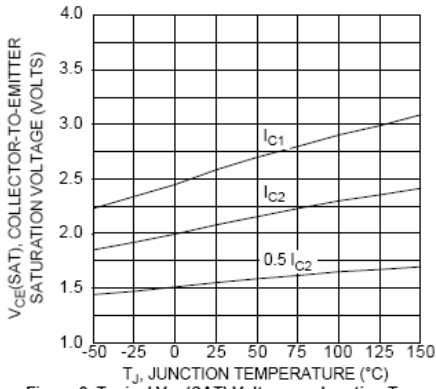


Figure 8, Typical $V_{CE(SAT)}$ Voltage vs Junction Temperature

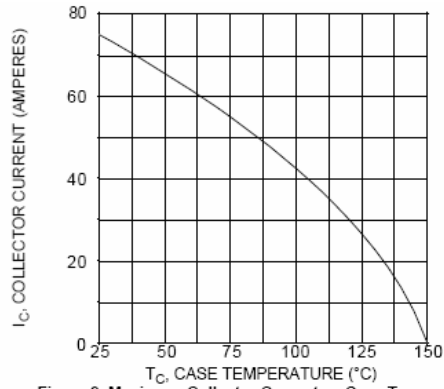


Figure 9, Maximum Collector Current vs Case Temperature

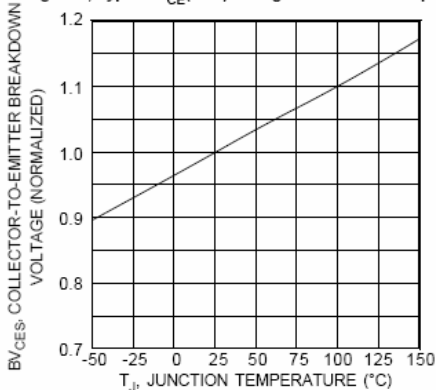


Figure 10, Breakdown Voltage vs Junction Temperature

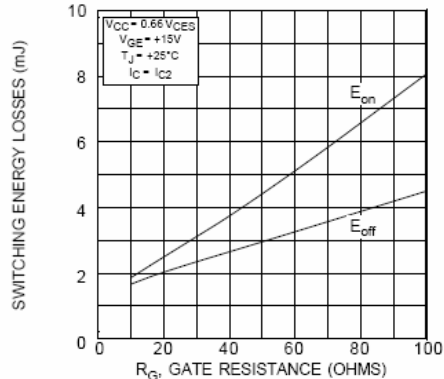


Figure 11, Typical Switching Energy Losses vs Gate Resistance

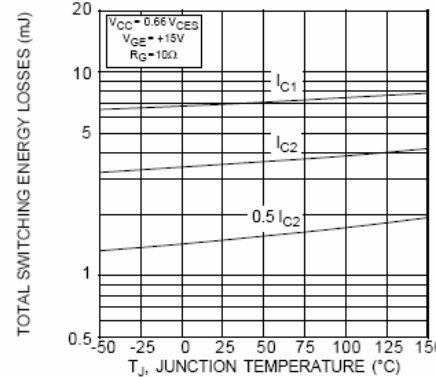


Figure 12, Typical Switching Energy Losses vs. Junction Temperature

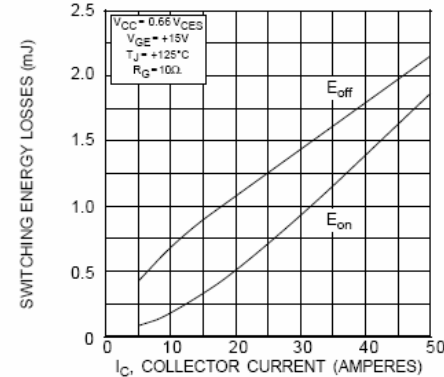


Figure 13, Typical Switching Energy Losses vs Collector Current

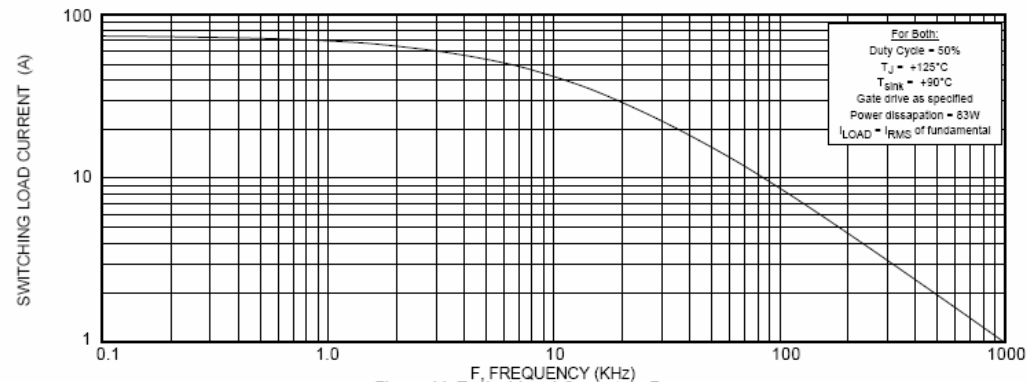


Figure 14, Typical Load Current vs Frequency

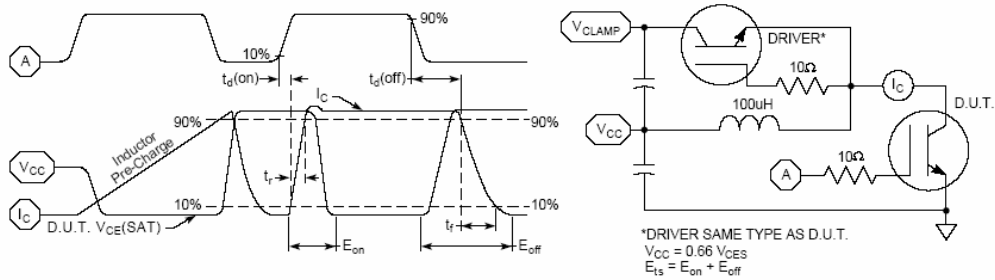


Figure 16, Switching Loss Test Circuit and Waveforms

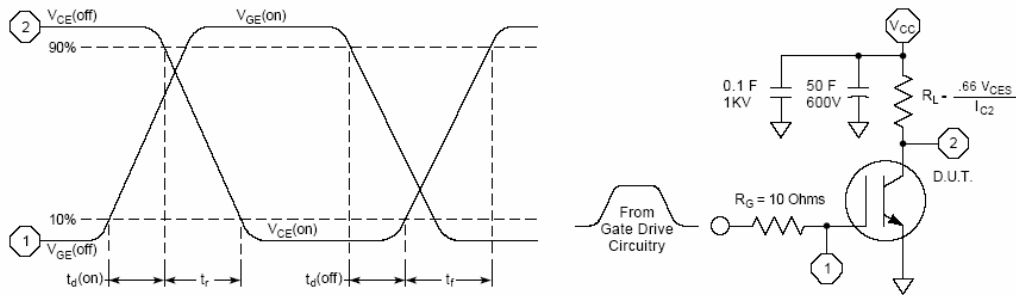


Figure 17, Resistive Switching Time Test Circuit and Waveforms

Typical Diode Performance Curve

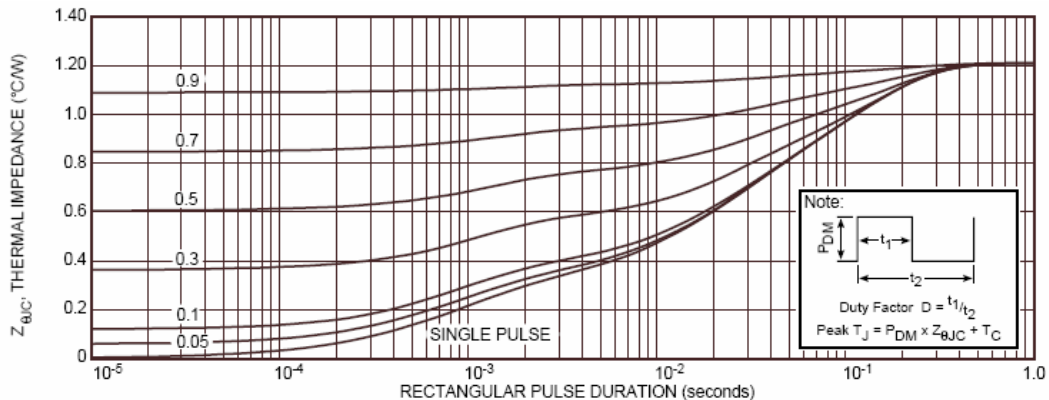


FIGURE 1a. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION

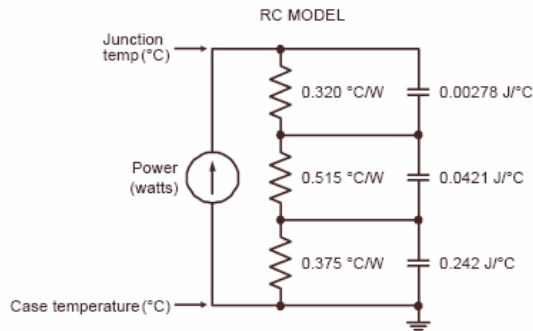


FIGURE 1b, TRANSIENT THERMAL IMPEDANCE MODEL

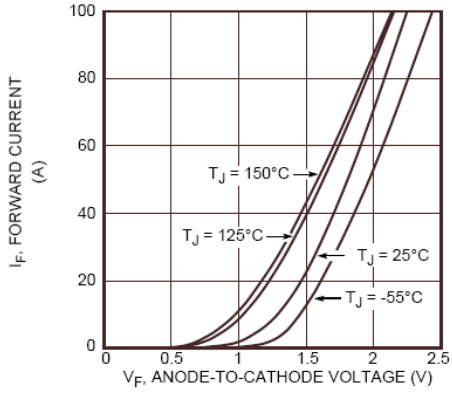


Figure 2. Forward Current vs. Forward Voltage

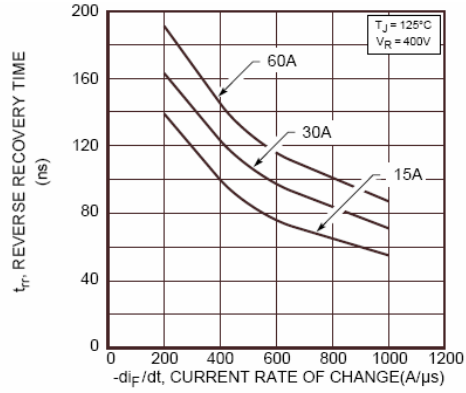


Figure 3. Reverse Recovery Time vs. Current Rate of Change

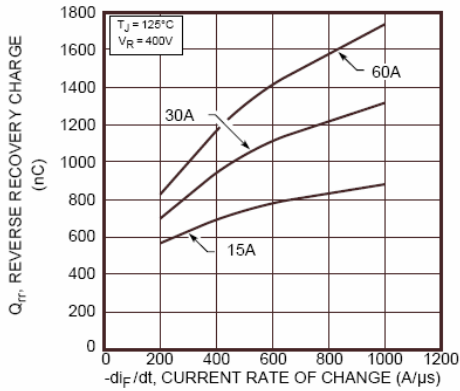


Figure 4. Reverse Recovery Charge vs. Current Rate of Change

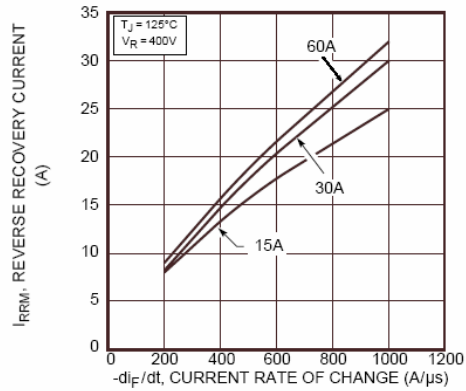


Figure 5. Reverse Recovery Current vs. Current Rate of Change

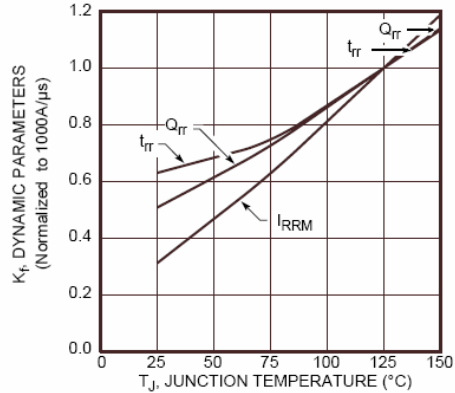


Figure 6. Dynamic Parameters vs. Junction Temperature

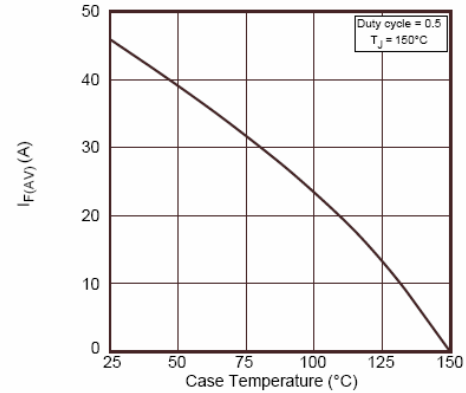


Figure 7. Maximum Average Forward Current vs. Case Temperature

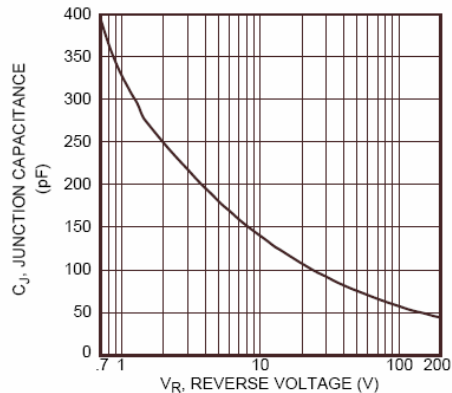


Figure 8. Junction Capacitance vs. Reverse Voltage

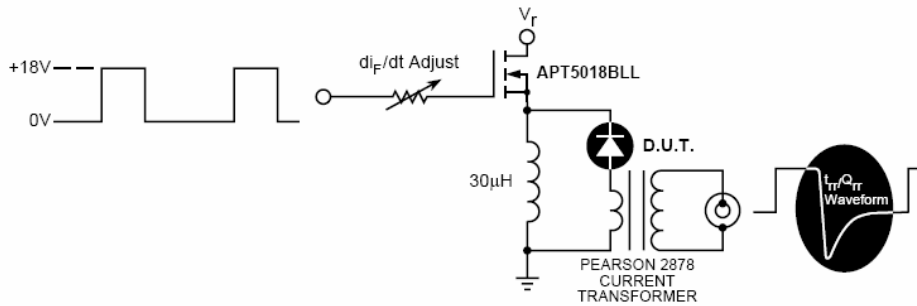


Figure 9. Diode Test Circuit

- 1 I_F - Forward Conduction Current
- 2 di_F/dt - Rate of Diode Current Change Through Zero Crossing.
- 3 I_{RRM} - Maximum Reverse Recovery Current.
- 4 t_{rr} - Reverse Recovery Time, measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through I_{RRM} and $0.25 \cdot I_{RRM}$ passes through zero.
- 5 Q_{rr} - Area Under the Curve Defined by I_{RRM} and t_{rr} .

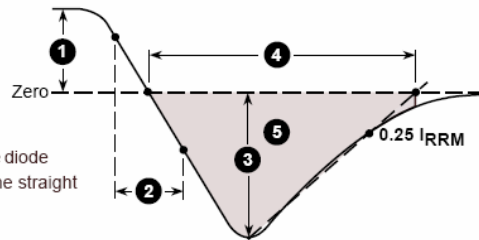
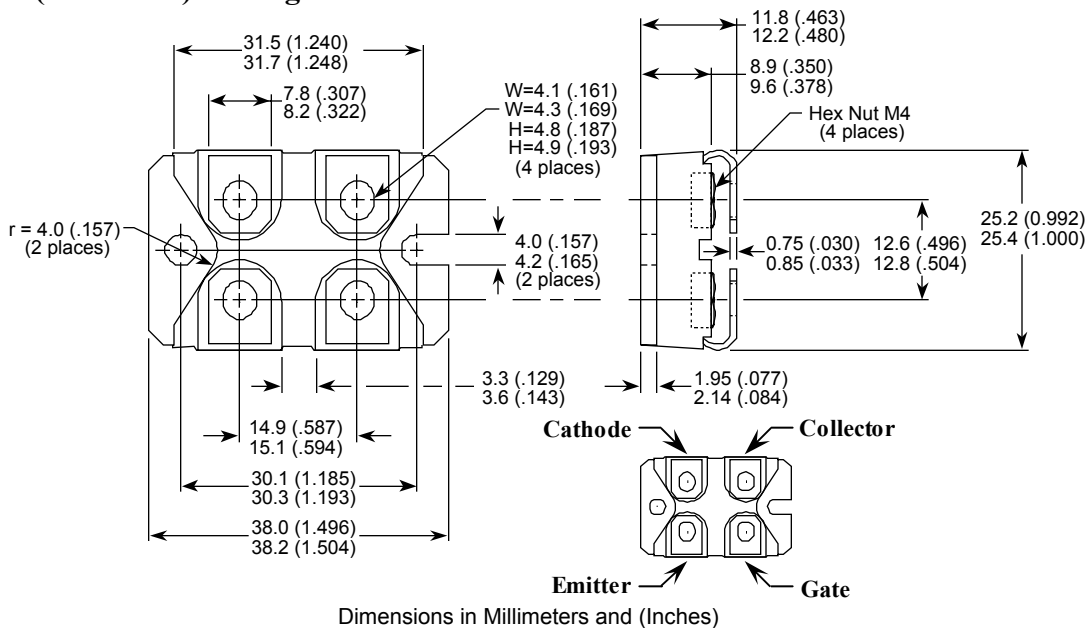


Figure 10. Diode Reverse Recovery Waveform and Definitions

SOT-227 (ISOTOP[®]) Package Outline



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Microsemi's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S. and Foreign patents pending. All Rights Reserved.